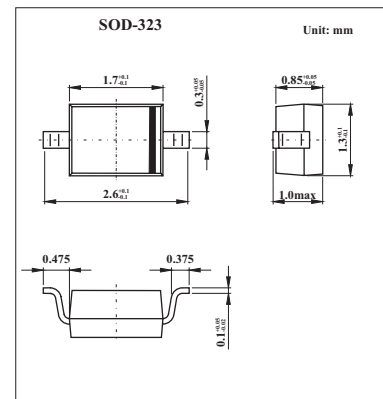


## Silicon Schottky Diode

## BAT62-03W

## ■ Features

- Low Barrier diode for detectors up to GHz frequencies

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	40	V
Forward current	$I_F$	40	mA
Junction current	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$
Total power dissipation	$P_{\text{tot}}$	100	mW
Junction ambient <sup>(1)</sup>	$R_{\text{thJA}}$	$\leq 650$	K/W
Junction-soldering point	$R_{\text{thJS}}$	$\leq 810$	K/W

Note:

1. Package mounted on an epoxy pcb 15 mm  $\times$  16.7mm  $\times$  0.7 mm

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown current	$I_R$	$V_R = 40\text{ V}, T_A = 25^\circ\text{C}$			10	$\mu\text{A}$
Forward voltage	$V_F$	$I_F = 2\text{ mA}$		0.58	1	V
Diode capacitance	$C_T$	$V_R = 0; f = 1\text{ MHz}$		0.35	0.6	pF
Case capacitance	$C_C$	$f = 1\text{ MHz}$		0.1		pF
Differential forward resistance	$R_O$	$V_R = , f = 10\text{ kHz}$		225		k $\Omega$
Series inductance chip to ground	$L_S$			2		nH

## ■ Marking

Marking	L
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